

# INTERNATIONAL STANDARD

## NORME INTERNATIONALE

**Semiconductor devices – Non-destructive recognition criteria of defects in  
silicon carbide homoepitaxial wafer for power devices –  
Part 3: Test method for defects using photoluminescence**

**Dispositifs à semiconducteurs – Critères de reconnaissance non destructifs des  
défauts au sein d'une plaquette homoépitaxiale de carbure de silicium pour des  
dispositifs d'alimentation –  
Partie 3: Méthode d'essai pour les défauts à l'aide de la photoluminescence**



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IEC Central Office  
3, rue de Varembe  
CH-1211 Geneva 20  
Switzerland

Tel.: +41 22 919 02 11  
[info@iec.ch](mailto:info@iec.ch)  
[www.iec.ch](http://www.iec.ch)

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## INTERNATIONAL ELECTROTECHNICAL COMMISSION

# **SEMICONDUCTOR DEVICES – NON-DESTRUCTIVE RECOGNITION CRITERIA OF DEFECTS IN SILICON CARBIDE HOMOEPITAXIAL WAFER FOR POWER DEVICES –**

## **Part 3: Test method for defects using photoluminescence**

### **FOREWORD**

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International Standard IEC 63068-3 has been prepared by IEC technical committee 47: Semiconductor devices.

The text of this International Standard is based on the following documents:

|              |                  |
|--------------|------------------|
| FDIS         | Report on voting |
| 47/2628/FDIS | 47/2638/RVD      |

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 63068 series, published under the general title *Semiconductor devices – Non-destructive recognition criteria of defects in silicon carbide homoepitaxial wafer for power devices*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

## INTRODUCTION

Silicon carbide (SiC) is widely used as a semiconductor material for next-generation power semiconductor devices. SiC, as compared with silicon (Si), has superior physical properties such as a higher breakdown electric field, higher thermal conductivity, lower thermal generation rate, higher saturated electron drift velocity, and lower intrinsic carrier concentration. These attributes realize SiC-based power semiconductor devices with faster switching speeds, lower losses, higher blocking voltages, and higher temperature operation relative to standard Si-based power semiconductor devices.

SiC-based power semiconductor devices are not fully realized due to some issues including high costs, low yield, and low long-term reliability. In particular, one of the serious issues lies in the defects existing in SiC homoepitaxial wafers. Although efforts of decreasing defects in SiC homoepitaxial wafers are actively implemented, there are a number of defects in commercially available SiC homoepitaxial wafers. Therefore, it is indispensable to establish an international standard regarding the quality assessment of SiC homoepitaxial wafers.

The IEC 63068 series of standards is planned to comprise Part 1, Part 2, and Part 3, as detailed below. This document provides definitions and guidance in use of photoluminescence for detecting defects in commercially available silicon carbide (SiC) homoepitaxial wafers.

Part 1: Classification of defects

Part 2: Test method for defects using optical inspection

Part 3: Test method for defects using photoluminescence

# **SEMICONDUCTOR DEVICES – NON-DESTRUCTIVE RECOGNITION CRITERIA OF DEFECTS IN SILICON CARBIDE HOMOEPITAXIAL WAFER FOR POWER DEVICES –**

## **Part 3: Test method for defects using photoluminescence**

### **1 Scope**

This part of IEC 63068 provides definitions and guidance in use of photoluminescence for detecting as-grown defects in commercially available 4H-SiC (Silicon Carbide) epitaxial wafers. Additionally, this document exemplifies photoluminescence images and emission spectra to enable the detection and categorization of the defects in SiC homoepitaxial wafers.

### **2 Normative references**

There are no normative references in this document.

### **3 Terms and definitions**

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

#### **3.1 photoluminescence PL**

emission of light from materials as a subsequence of electronic excitation by absorption of photons

#### **3.2 photoluminescence imaging PL imaging**

technique for capturing, processing and analysing images of defects using light source for electronic excitation, focusing optics, optical filter, optical image sensor and computer systems

#### **3.3 focusing optics**

lens system used for magnifying and capturing optical images

#### **3.4 optical filter**

optical component designed to transmit only a specific wavelength region and to block other regions

#### **3.5 optical image sensor**

device to transform an optical image into digital data